

### Schottky Barrier Diode

**B5817W-B5819W**

#### FEATURES

- Extremely low  $V_F$ .
- Low stored charge,majority carrier conduction.
- Low power loss/high efficient



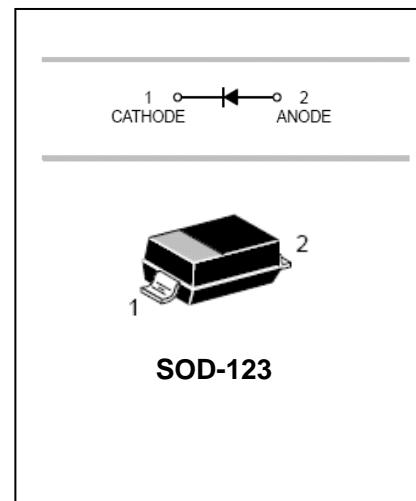
Lead-free

#### APPLICATIONS

- For Use In Low Voltage, High Frequency Inverters.
- Free Wheeling, And Polarity Protection Applications.

#### ORDERING INFORMATION

Type No.	Marking	Package Code
B5817W	SJ	SOD-123
B5818W	SK	SOD-123
B5819W	SL	SOD-123



**MAXIMUM RATING @  $T_a=25^\circ\text{C}$  unless otherwise specified**

Parameter	symbol	B5817W	B5818W	B5819W	Unit
Non-Repetitive Peak reverse voltage	$V_{RSM}$	24	36	48	V
Peak repetitive Peak reverse voltage	$V_{RRM}$				
Working Peak Reverse voltage	$V_{RWM}$	20	30	40	V
DC Reverse Voltage	$V_R$				
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average Rectified output Current	$I_o$	1			A
Peak forward surge current@=8.3ms	$I_{FSM}$	25			A
Power Dissipation	$P_d$	250			mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	80			$^\circ\text{C}/\text{W}$
Storage temperature	$T_J, T_{STG}$	-65~+125			$^\circ\text{C}$

# Diode Semiconductor Korea

## Schottky Barrier Diode

**B5817W-B5819W**

ELECTRICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified

Parameter	Symbol	Test Condition	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(\text{BR})}$	$I_R=1\text{mA}$ B5817W B5818W B5819W	20 30 40		V
Reverse voltage leakage current	$I_R$	$V_R=20\text{V}$ $V_R=30\text{V}$ $V_R=40\text{V}$	B5817W B5818W B5819W		1 mA
Forward voltage	$V_F$	B5817W B5818W B5819W	$I_F=1\text{A}$ $I_F=3\text{A}$ $I_F=1\text{A}$ $I_F=3\text{A}$ $I_F=1\text{A}$ $I_F=3\text{A}$	0.45 0.75 0.55 0.875 0.6 0.9	V
Diode capacitance	$C_D$	$V_R=4\text{V}, f=1\text{MHz}$		120	pF

TYPICAL CHARACTERISTICS @  $T_a=25^\circ\text{C}$  unless otherwise specified

Fig. 1 - Forward Current Derating Curve

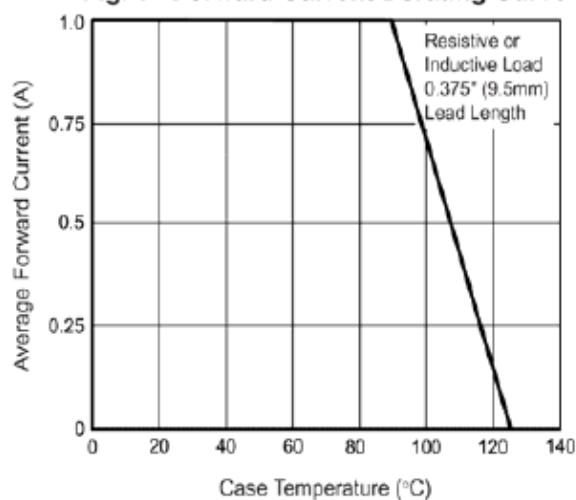
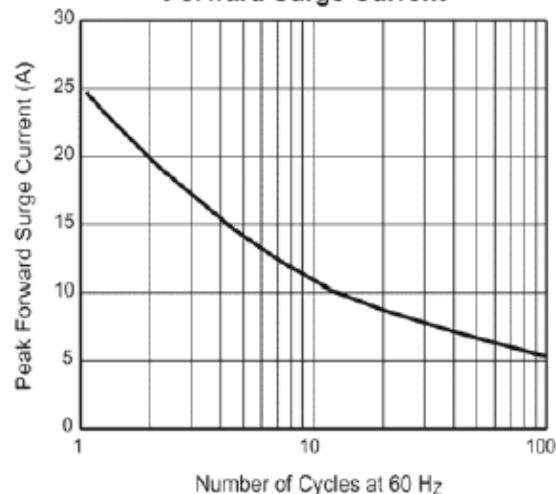
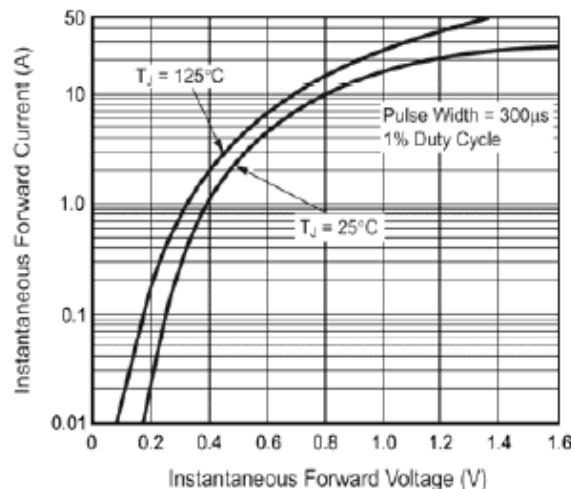


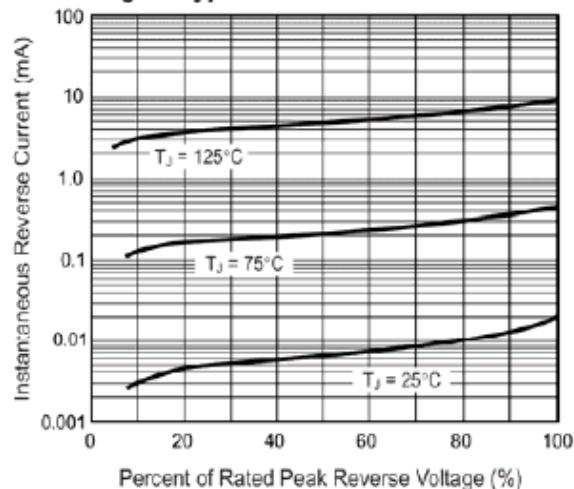
Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current



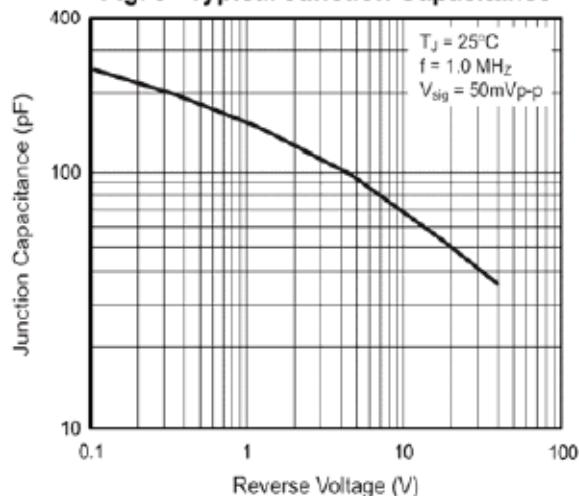
**Fig. 3 - Typical Instantaneous Forward Characteristics**



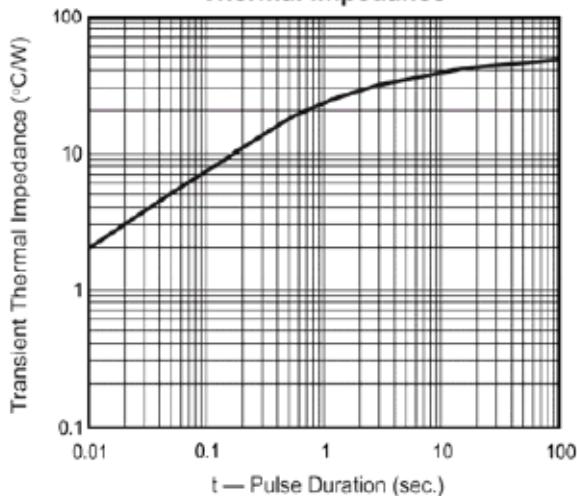
**Fig. 4 - Typical Reverse Characteristics**



**Fig. 5 - Typical Junction Capacitance**



**Fig. 6 - Typical Transient Thermal Impedance**



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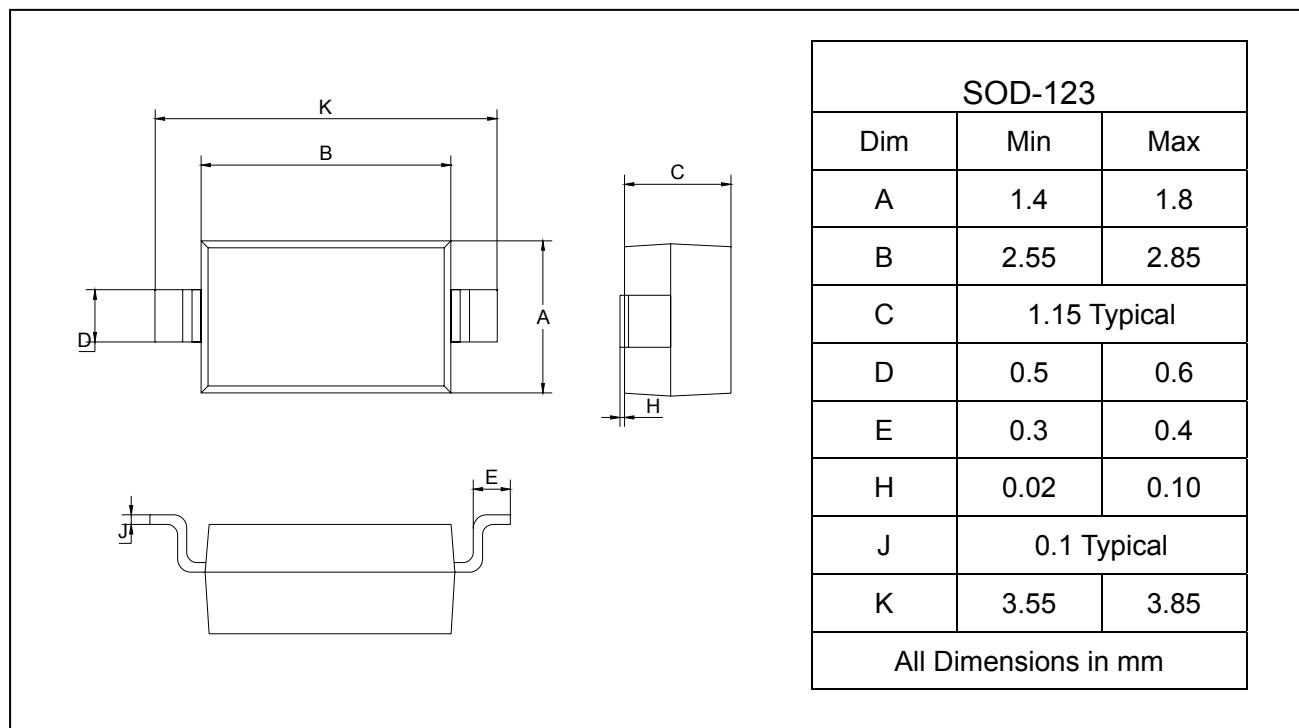
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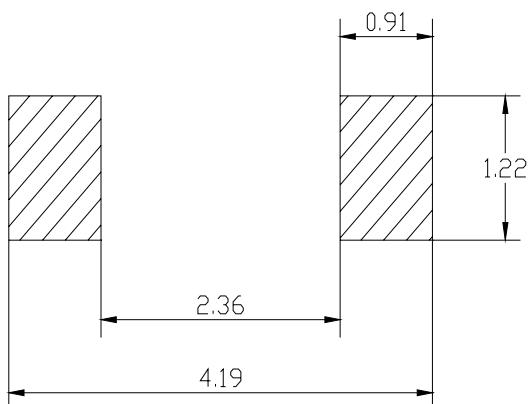
### PACKAGE OUTLINE

Plastic surface mounted package

SOD-123



### SOLDERING FOOTPRINT



Unit: mm

### PACKAGE INFORMATION

Device	Package	Shipping
B5817W-B5819W	SOD-123	3000/Tape&Reel